High Current Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector - Emitter Voltage	BC635 BC637 BC639	V _{CEO}	45 60 80	Vdc
Collector - Base Voltage	BC635 BC637 BC639	V _{СВО}	45 60 80	Vdc
Emitter - Base Voltage		V _{EBO}	5.0	Vdc
Collector Current – Continuous		Ic	1.0	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C		P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C		P _D	800 12	mW mW/°C
Operating and Storage Junction Temperature Range		T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

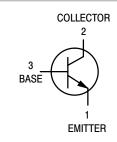
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction–to–Case	$R_{ heta JC}$	83.3	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



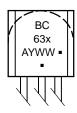
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



BC63x = Device Code x = 5, 7, or 9

A = Assembly Location

Y = Year WW = Work Week • Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•		•	
Collector – Emitter Breakdown Voltage (Note 1) $ (I_C = 10 \; \mu \text{Adc}, \; I_B = 0) \\ \text{BC635} \\ \text{BC637} \\ \text{BC639} $	V _(BR) CEO	45 60 80	- - -	- - -	Vdc
Collector – Emitter Zero–Gate Breakdown Voltage(Note 1) $(I_C = 100 \; \mu \text{Adc}, I_B = 0) \\ BC639-16$	V _{(BR)CES}	120	-	-	Vdc
Collector – Base Breakdown Voltage $(I_C = 100 \; \mu \text{Adc}, I_E = 0) \\ \text{BC635} \\ \text{BC637} \\ \text{BC639}$	V _(BR) CBO	45 60 80	- - -	- - -	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc$, $I_C = 0$)	V _{(BR)EBO}	5.0	_	_	Vdc
Collector Cutoff Current $(V_{CB} = 30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 30 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$	I _{CBO}	- -	- -	100 10	nAdc μAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain $ \begin{aligned} &\text{(I}_C=5.0 \text{ mAdc, V}_{CE}=2.0 \text{ Vdc)} \\ &\text{(I}_C=150 \text{ mAdc, V}_{CE}=2.0 \text{ Vdc)} \end{aligned} \qquad &\text{BC635} \\ &\text{BC637} \\ &\text{BC639} \\ &\text{BC639}-16\text{ZLT1} \end{aligned} $	h _{FE}	25 40 40 40 40		- 250 160 160 250	-
$(I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V})$		25	_	-	
Collector – Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$)	V _{CE(sat)}	-	-	0.5	Vdc
Base – Emitter On Voltage ($I_C = 500 \text{ mAdc}$, $V_{CE} = 2.0 \text{ Vdc}$)	V _{BE(on)}	-	-	1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain – Bandwidth Product (I _C = 50 mAdc, V _{CE} = 2.0 Vdc, f = 100 MHz)	f _T	-	200	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	-	7.0	-	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ib}	_	50	-	pF

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle 2.0%.

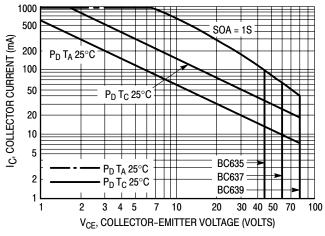


Figure 1. Active Region Safe Operating Area

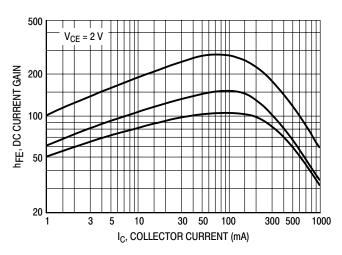


Figure 2. DC Current Gain

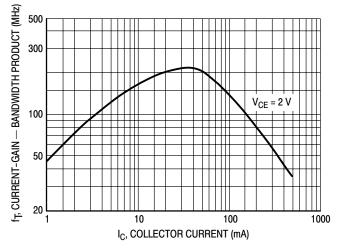


Figure 3. Current-Gain — Bandwidth Product

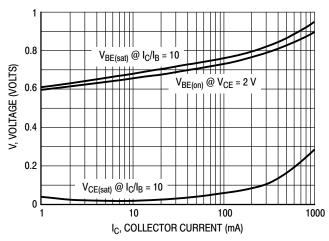


Figure 4. "Saturation" and "On" Voltages

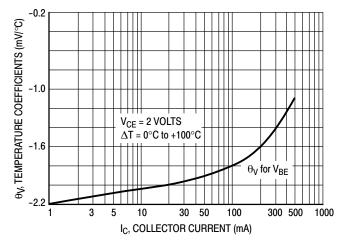


Figure 5. Temperature Coefficients

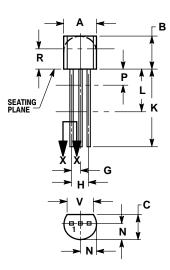
DEVICE ORDERING INFORMATION

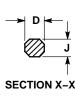
Device	Package	Shipping [†]	
BC635RL1	TO-92	2000 / Tape & Reel	
BC635RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel	
BC635ZL1	TO-92	2000 / Tape & Reel	
BC635ZL1G	TO-92 (Pb-Free)	2000 / Tape & Reel	
BC637	TO-92	5000 Units / Box	
BC637G	TO-92 (Pb-Free)	5000 Units / Box	
BC639	TO-92	5000 Units / Box	
BC639G	TO-92 (Pb-Free)	5000 Units / Box	
BC639RL1	TO-92	2000 / Tape & Reel	
BC639RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel	
BC639ZL1	TO-92	2000 / Ammo Box	
BC639ZL1G	TO-92 (Pb-Free)	2000 / Ammo Box	
BC639-16ZL1	TO-92	2000 / Ammo Box	
BC639-16ZL1G	TO-92 (Pb-Free)	2000 / Ammo Box	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AL





NOTES:

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- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3 //3	

STYLE 14:

PIN 1. EMITTER

COLLECTOR
 BASE

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